350 kHz, Low Power, Zero-Drift, CMOS, Rail-to-Rail Operational Amplifier with RF Filter Advanced

1. Features

- Single-Supply Operation from +2.5V ~ +5.5V
- Rail-to-Rail Input / Output
- Gain-Bandwidth Product: 350 kHz (Typ.)
- Quiescent Current per Amplifier: 20µA (Typ.)
- Zero Drift: 0.05µV/°C (Max.)
- Low Offset Voltage: 20µV (Max. @25°C)
- Low Input Bias Current: 10pA (Typ. @25°C)

2. General Description

The GT7131/GT7132 amplifier is single/dual supply, micro-power, zero-drift CMOS operational amplifiers, the amplifiers offer bandwidth of 350 kHz, rail-to-rail inputs and outputs, and single-supply operation from 2.5V to 5.5V. GT7131/GT7132 uses chopper stabilized technique to provide very low offset voltage (less than $20\mu V$ maximum) and near zero drift over temperature. Low quiescent supply current of $20\mu A$ per amplifier and very

3. Applications

- Portable Equipment
- Mobile Communications
- Filter and Buffer
- Sensor Interface

- Slew Rate: 0.1V/µs (Typ.)
- Total Harmonic Distortion plus Noise: 0.005 % (Typ.)
- Embedded RF Anti-EMI Filter
- Operating Temperature: -40°C ~ +125°C
- GT7131 Available in SOT23-5 and SOP8 Packages
- GT7132 available in SOP8 and MSOP8 Packages
- •

low input bias current of 10pA make the devices an ideal choice for low offset, low power consumption and high impedance applications.

The GT7131 is available in SOT23-5 and SOP8 packages. And the GT7132 is available in SOP8 and MSOP8 packages. The extended temperature range of -40°C to +125°C over all supply voltages offers additional design flexibility.

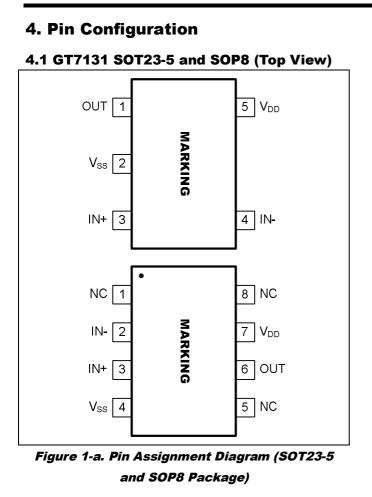
- Medical Instrumentation
- Battery-Powered Instruments
- Handheld Test Equipment

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4.2 GT7132 SOP8 and MSOP8 (Top View)

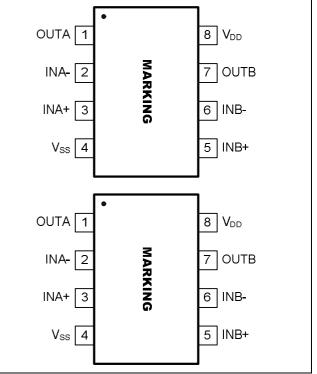


Figure 2-b. Pin Assignment Diagram (SOP8 and MSOP8 Package)

Note: Please see section "Part Markings" for detailed Marking Information.



5. Electrical Characteristics

5.1 Absolute Maximum Ratings

Condition	Min	Max				
Power Supply Voltage	-0.5V	+7V				
(V _{DD} to Vss)	-0.5V	+ <i>1</i> V				
Analog Input Voltage	Vss-0.5V	Vpp+0.5V				
(IN+ or IN-)	VSS-0.5V	VDD+0.3V				
PDB Input Voltage	Vss-0.5V	+7V				
Operating Temperature Range	-40°C	+125°C				
Junction Temperature	+150°C					
Storage Temperature Range	-65°C	+150°C				
Lead Temperature	+300°C					
(soldering, 10sec)						
Package Thermal Resistance (T _A =+25°C)						
SOP23-5, θ _{JA}	190°C					
SOP8, θ _{JA} 130°C						
MSOP8, θ _{JA}	210	0°C				

Note: Stress greater than those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

5.2 Electrical Characteristics

 $(V_{DD} = +5V, V_{SS} = 0V, V_{CM} = 0V, V_{OUT} = V_{DD}/2, R_L = 10K$ tied to $V_{DD}/2$, SHDNB = V_{DD} , $T_A = -40^{\circ}C$ to $+125^{\circ}C$, unless otherwise noted. Typical values are at $T_A = +25^{\circ}C$.) (Note 1)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Supply-Voltage Range	V _{DD}	Guaranteed by the PSRR test	2.5	-	5.5	V
Quiescent Supply Current (per Amplifier)	Ι _Q	$V_{DD} = 5V$	14	20	26	μA
Input Offset Voltage	Vos		-	-	±20	μV
Input Offset Voltage Tempco	$\Delta V_{OS} / \Delta T$		-	-	0.05	µV/°C
Input Bias Current	Ι _Β	(Note 2)	-	10	-	pА
Input Offset Current	los	(Note 2)	-	100	-	pА
Input Common-Mode Voltage Range	V _{CM}		-0.1	-	V _{DD} +0.1	V
Common Mada Dejection Datio	CMRR	V _{DD} =5.5 Vss-0.1V≤V _{CM} ≤V _{DD} +0.1V	90	110	-	dB
Common-Mode Rejection Ratio	CIVIRR	Vss≤V _{CM} ≤5V	95	115	-	dB
Power-Supply Rejection Ratio	PSRR	V _{DD} = +2.5V to +5.5V	85	105	-	dB
Open-Loop Voltage Gain	Av	V _{DD} =5V, R _L =10kΩ, 0.05V≤V _O ≤4.95V	100	120	-	dB



Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Output Voltage Swing	V _{OUT}	$ V_{\text{IN+}}-V_{\text{IN-}} \geq$ 10mV, R_L = 100k\Omega to		G		m) (
		V _{DD} /2, V _{DD} -V _{OH}	-	6	-	mV
		$ V_{\text{IN+}}-V_{\text{IN-}} \ge 10 \text{mV}, \text{ R}_{\text{L}}$ = 100k Ω to		C		
		$V_{DD}/2, V_{OL}-V_{SS}$	-	6	-	mV
		$ V_{IN+}-V_{IN-} \geq 10 mV, R_L = 5 k\Omega$ to		60		mV
		V _{DD} /2, V _{DD} -V _{OH}	-	60	-	mv
		$ V_{\text{IN+}}-V_{\text{IN-}} ~\geq~ 10 mV, ~R_L ~=~ 5 k\Omega ~to$		60		mV
		$V_{DD}/2, V_{OL}-V_{SS}$	-	00	-	mv
Output Short-Circuit Current	I _{SC}	Sinking or Sourcing	-	±5	-	mA
Gain Bandwidth Product	GBW	$A_V = +1V/V$	-	350	-	kHz
Slew Rate	SR	$A_V = +1V/V$	-	0.1	-	V/µs
Settling Time	+	To 0.1%, V _{OUT} = 2V step		20		μs
Setting Time	ts	$A_V = +1V/V$	-	20	-	
Over Load Recovery Time		$V_{\text{IN}} \times Gain \text{=} V_{\text{S}}$	-	100	-	μs
Input Voltage Noise Density	_	f = 1kHz	-	70	-	nV/√Hz
Input voltage Noise Density	en	<i>f</i> = 10kHz	-	60	-	Πν/ΝΗΖ
		$V_{OUT} = 2V_{PP}, Av = +1V/V,$		0.005		0/
Total Harmonic Distortion plus		$R_L = 10k\Omega$ to GND, $f = 1kHz$	-	0.005	-	
Noise	THD+N	$V_{OUT} = 2V_{PP}, Av = +1V/V,$		0.1	-	%
		R_{L} =10kΩ to GND, f = 10kHz	-	0.1		

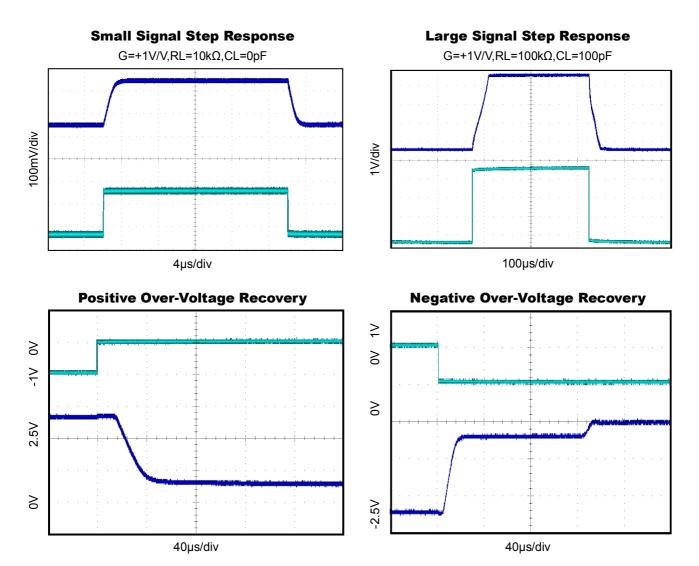
Note 1: All devices are 100% production tested at $T_A = +25^{\circ}C$; all specifications over the automotive temperature range is guaranteed by design, not production tested.

Note 2: Parameter is guaranteed by design.

F

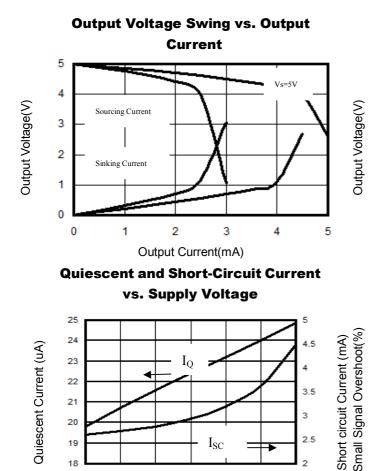
5.3 Typical characteristics

(T_A=+25°C, R_L=10 k\Omega connected to V_S/2 and V_OUT= V_S/2, unless otherwise noted.)





Typical characteristics (Continued)



Supply Voltage (V)

4

4.5

5

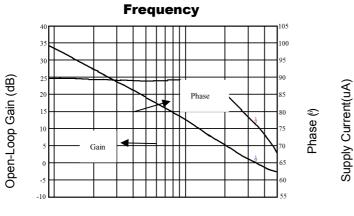
5.5



3.5

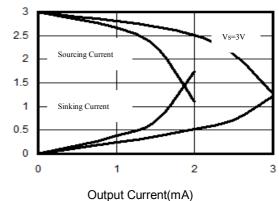
2.5

3

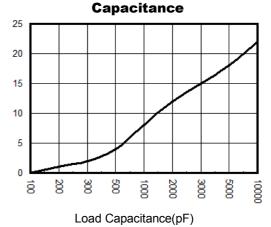


Frequency (Hz)

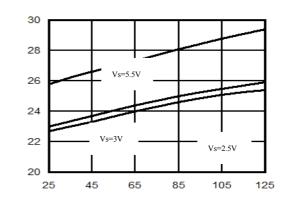
Output Voltage Swing vs. Output Current



Small Signal Overshoot vs. Load



Supply Current vs. Temperature



Temperature(°C)



6. Application Information

6.1 Size

GT7131/GT7132 series op amps are unity-gain stable and suitable for a wide range of general-purpose applications. The small footprints of the GT7131/GT7132 series packages save space on printed circuit boards and enable the design of smaller electronic products.

6.2 Power Supply Bypassing and Board Layout

GT7131/GT7132 series operates from a single 2.5V to 5.5V supply or dual $\pm 1.25V$ to $\pm 2.75V$ supplies. For best performance, a 0.1μ F ceramic capacitor should be placed close to the V_{DD} pin in single supply operation. For dual supply operation, both V_{DD} and V_{SS} supplies should be bypassed to ground with separate 0.1μ F ceramic capacitors.

6.3 Low Supply Current

The low supply current (typical $20\mu A/40\mu A$) of GT7131/GT7132 series will help to maximize battery life. They are ideal for battery powered systems

6.4 Operating Voltage

GT7131/GT7132 series operate under wide input supply voltage (2.5V to 5.5V). In addition, all temperature specifications apply from -40 °C to +125 °C. Most behavior remains unchanged throughout the full operating voltage range. These guarantees ensure operation throughout the single Li-Ion battery lifetime

6.5 Rail-to-Rail Input

The input common-mode range of GT7131/GT7132 series extends 100mV beyond the supply rails (V_{SS} -0.1V to V_{DD} +0.1V). This is achieved by using complementary input stage. For normal operation, inputs should be limited to this range.

6.6 Rail-to-Rail Output

Rail-to-Rail output swing provides maximum possible dynamic range at the output. This is particularly important when operating in low supply voltages. The output voltage of GT7131/GT7132series can typically swing to less than 10mV from supply rail in light resistive loads (>100k Ω), and 60mV of supply rail in moderate resistive loads (5k Ω).

6.7 Capacitive Load Tolerance

The GT7131/GT7132 series can directly drive 250pF capacitive load in unity-gain without oscillation. Increasing the gain enhances the amplifier's ability to drive greater capacitive loads. In unity-gain configurations, the capacitive load drive can be improved by inserting an isolation resistor R_{ISO} in series with the capacitive load, as shown in *Figure 2*.

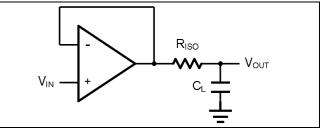


Figure 2. Indirectly Driving a Capacitive Load Using Isolation Resistor

The bigger the R_{ISO} resistor value, the more stable V_{OUT} will be. However, if there is a resistive load R_L in parallel with the capacitive load, a voltage divider (proportional to R_{ISO}/R_L) is formed, this will result in a gain error.

The circuit in **Figure 3** is an improvement to the one in **Figure 2**. R_F provides the DC accuracy by feed-forward the V_{IN} to R_L . C_F and R_{ISO} serve to counteract the loss of phase margin by feeding the high frequency component of the output signal back to the amplifier's inverting input, thereby preserving the phase margin in the overall feedback loop. Capacitive drive can be increased by increasing the value of C_F . This in turn will slow down the pulse response.



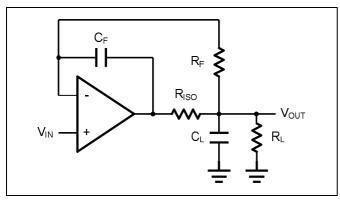


Figure 3. Indirectly Driving a Capacitive Load with DC Accuracy

6.8 Differential amplifier

The differential amplifier allows the subtraction of two input voltages or cancellation of a signal common the two inputs. It is useful as a computational amplifier in making a differential to single-end conversion or in rejecting a common mode signal. *Figure 4.* shown the differential amplifier using GT7131/GT7132.

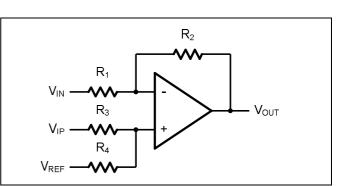


Figure 4. Differential Amplifier

$$V_{OUT} = \left(\frac{R_{I} + R_{2}}{R_{3} + R_{4}}\right) \frac{R_{4}}{R_{I}} V_{IN} - \frac{R_{2}}{R_{I}} V_{IP} + \left(\frac{R_{I} + R_{2}}{R_{3} + R_{4}}\right) \frac{R_{3}}{R_{I}} V_{REF}$$

If the resistor ratios are equal (i.e. $R_1=R_3$ and $R_2=R_4$), then

$$V_{OUT} = \frac{R_2}{R_I} (V_{IP} - V_{IN}) + V_{REF}$$

6.9 Instrumentation Amplifier

The input impedance of the previous differential amplifier is set by the resistors R1, R2, R3, and R4. To maintain the high input impedance, one can use a voltage follower in front of each input as shown in the following two instrumentation amplifiers.

6.10 Three-Op-Amp Instrumentation Amplifier

The dual GT7132 can be used to build a three-op-amp instrumentation amplifier as shown in *Figure 5*.



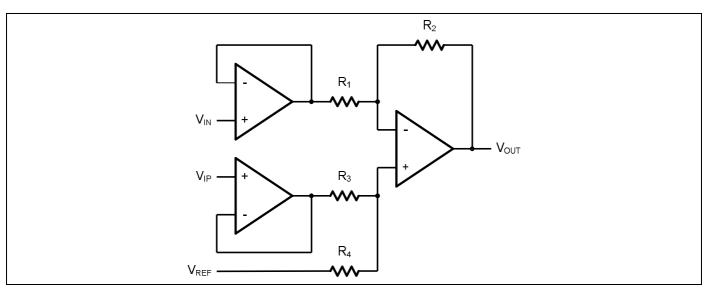


Figure 5. Three-Op-Amp Instrumentation Amplifier

The amplifier in **Figure 5** is a high input impedance differential amplifier with gain of R_2/R_1 . The two differential voltage followers assure the high input impedance of the amplifier.

6.11 Two-Op-Amp Instrumentation Amplifier

GT7131/GT7132 can also be used to make a high input impedance two-op-amp instrumentation amplifier as shown in *Figure 6*.

 $VOUT = (1 + \frac{R_4}{R_3})(V_{IP} - V_{IN})$

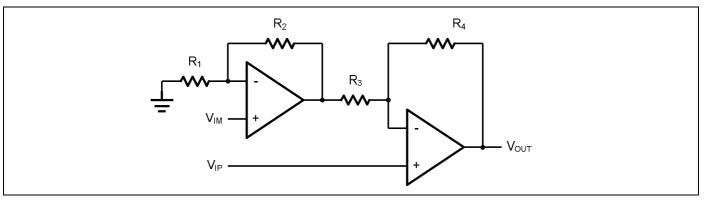


Figure 6. Two-Op-Amp Instrumentation Amplifier

Where $R_1=R_3$ and $R_2=R_4$. If all resistors are equal, then

 $V_{OUT}=2(V_{IP}-V_{IN})$



6.12 Single-Supply Inverting Amplifier

The inverting amplifier is shown in **Figure 7**. The capacitor C_1 is used to block the DC signal going into the

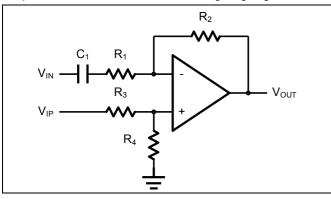
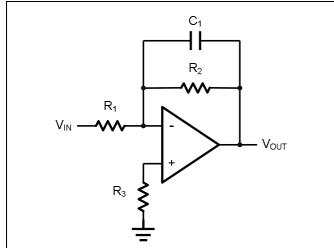


Figure 7. Single Supply Inverting Amplifier

6.13 Low Pass Active Filter

The low pass active filter is shown in **Figure 8**. The DC gain is defined by $-R_2/R_1$. The filter has a -20dB/decade roll-off after its corner frequency $f_C=1/(2\pi R_3 C_1)$.





6.14 Sallen-Key 2nd Order Active Low-Pass Filter

GT7131/GT7132 can be used to form a 2^{nd} order Sallen-Key active low-pass filter as shown in *Figure 9*. The transfer function from V_{IN} to V_{OUT} is given by

$$\frac{V_{OUT}}{V_{IN}}(S) = \frac{\frac{1}{C_{I}C_{2}R_{I}R_{2}}A_{LP}}{S^{2} + S(\frac{1}{C_{I}R_{1}} + \frac{1}{C_{I}R_{2}} + \frac{1}{C_{2}R_{2}} - \frac{A_{LP}}{C_{2}R_{2}}) + \frac{1}{C_{I}C_{2}R_{I}R_{2}}}$$

Where the DC gain is defined by $A_{LP}=l+R_3/R_4$, and the corner frequency is given by

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AC signal source V_{IN}. The value of R₁ and C₁ set the cut-off frequency to $f_C=1/(2\pi R_1C_1)$. The DC gain is defined by $V_{OUT}=-(R_2/R_1)V_{IN}$

$$\omega C = \sqrt{\frac{l}{C_l C_2 R_l R_2}}$$

The pole quality factor is given by

$$\frac{\omega C}{Q} = \frac{1}{C_1 R_1} + \frac{1}{C_1 R_2} + \frac{1}{C_2 R_2} - \frac{A_{LP}}{C_2 R_2}$$

Let R1=R2=R and C1=C2=C, the corner frequency and the pole quality factor can be simplified as below

$$\omega_C = \frac{1}{CR}$$

And $Q=2-R_3/R_4$

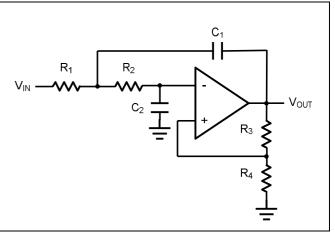


Figure 9. Sanllen-Key 2nd Order Active Low-Pass Filter

6.15 Sallen-Key 2nd Order high-Pass Active Filter

The 2^{nd} order Sallen-key high-pass filter can be built by simply interchanging those frequency selective components R₁, R₂, C₁, and C₂ as shown in *Figure 10*.



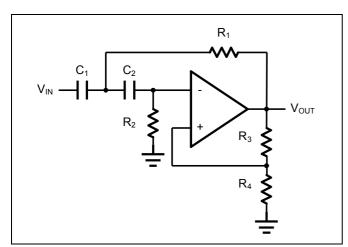


Figure 10. Sanllen-Key 2nd Order Active High-Pass Filter

$$\frac{V_{OUT}}{V_{IN}}(S) = \frac{S^2 A_{HP}}{S^2 + S(\frac{1}{C_I R_I} + \frac{1}{C_2 R_2} + \frac{1 - A_{HP}}{C_I R_I}) + \frac{1}{C_I C_2 R_I R_2}}$$

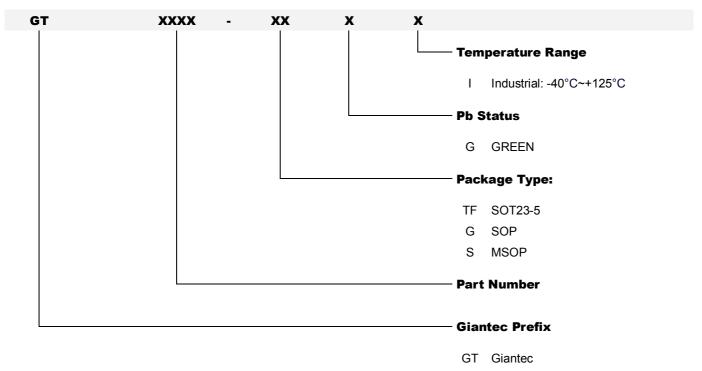
Where $A_{HP} = l + R_3/R_4$

6.16 Input Offset Cancellation

The GT7131/GT7132 series opamps use internal chopping stabilized technique to cancel dc offset and flick noise. Since the offset temperature drift is a dc parameter, it is also cancelled by the chopping technique. The amplifier requires approximately 100 μ s to achieve the specified V_{os} accuracy.



7. Ordering Information



Order Number	Package Description	Package Option
GT7131-TFGI-TR	SOT23-5	Tape and Reel 3000
GT7131-GGI-TR	SOP8	Tape and Reel 4000
GT7132-GGI-TR	SOP8	Tape and Reel 4000
GT7132-SGI-TR	MSOP8	Tape and Reel 4000



8. Part Markings

8.1 GT7131-TFGI (Top View)

			3	<u> </u>	<u>Y</u>	w		
131		GT7131-TFG	.1					
•		Pin 1 Indicato						
Y		Seal Year		w		Se	al Week	
- 2010 (1st half ye	ear)	A		Week 01		A		
2010 (2nd half y		В		Week 02		В		
2011 (1st half ye		С						
2011 (2nd half y		D		Week 26		Z		
2012 (1st half ye		E		Week 27		А		
2012 (2nd half y		F		Week 28		В		
2022 (2nd half y	ear)	Z		Week 52		Z		
8.2 GT7131-	GGI (Top V	'iew)						
G	<u> </u>	7	1	3	1	G	G	<u> </u>
			Lo	t Number				
		v	V	14/		•		
•		<u>Y</u>	Y	w	<u>w</u>	<u>S</u>	<u>v</u>	
GT7131GGI						02 = Week 2		
Lot Number States the last 9 characters of the wafer								
lot information								
•	Pin 1 Indicator							
YY	Seal Year					51 = Week 51		
	00 = 2000					52 = Week 52		

S

V

01 = 2001

99 = 2099

Seal Week

01 = Week 1

ww

Subcon Code

J = ASESH

L = ASEKS

Die Version



8.3 GT7132-GGI (Top View)

G	<u> </u>	7		3	2	G	G	<u> </u>
				Lot <u>Num</u> ber				
•		<u> </u>	<u> </u>	W	w	S	<u>v</u>	

GT7132GGI			02 = Week 2
Lot Number	States the last 9 characters of the wafer		
	lot information		
•	Pin 1 Indicator		
YY	Seal Year		51 = Week 51
	00 = 2000		52 = Week 52
	01 = 2001	S	Subcon Code
	99 = 2099		J = ASESH
ww	Seal Week		L = ASEKS
	01 = Week 1	V	Die Version
0 4 0 7 7 4 0 0			

8.4 GT7132-SGI (Top View)

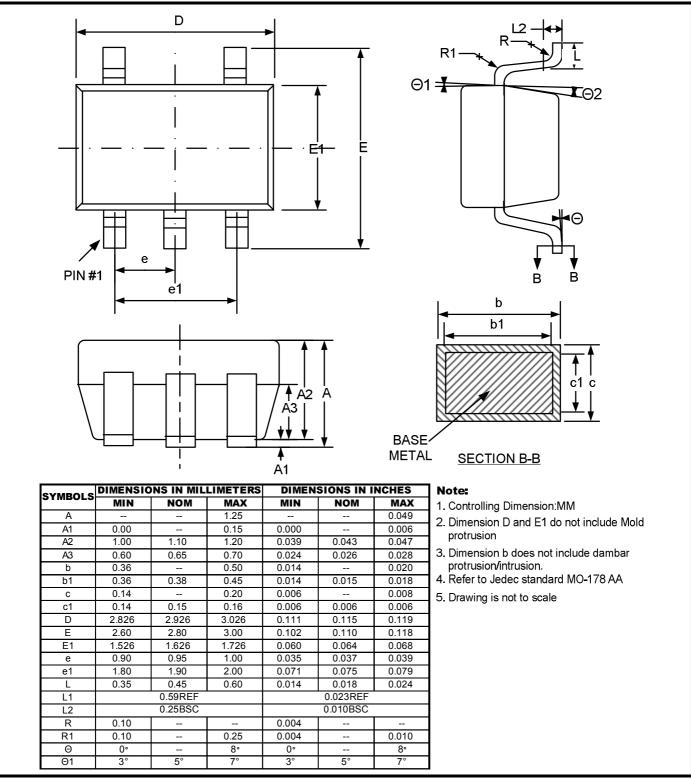
G	<u> </u>	7	1	3	2			
				Lot <u>Num</u> ber				
•		Y	Y	w	w	S	V	

GT7132	GT7132-SGI		02 = Week 2
Lot Number	States the last 9 characters of the wafer		
	lot information		
•	Pin 1 Indicator		
YY	Seal Year		51 = Week 51
	00 = 2000		52 = Week 52
	01 = 2001	S	Subcon Code
	99 = 2099		J = ASESH
ww	Seal Week		L = ASEKS
	01 = Week 1	V	Die Version



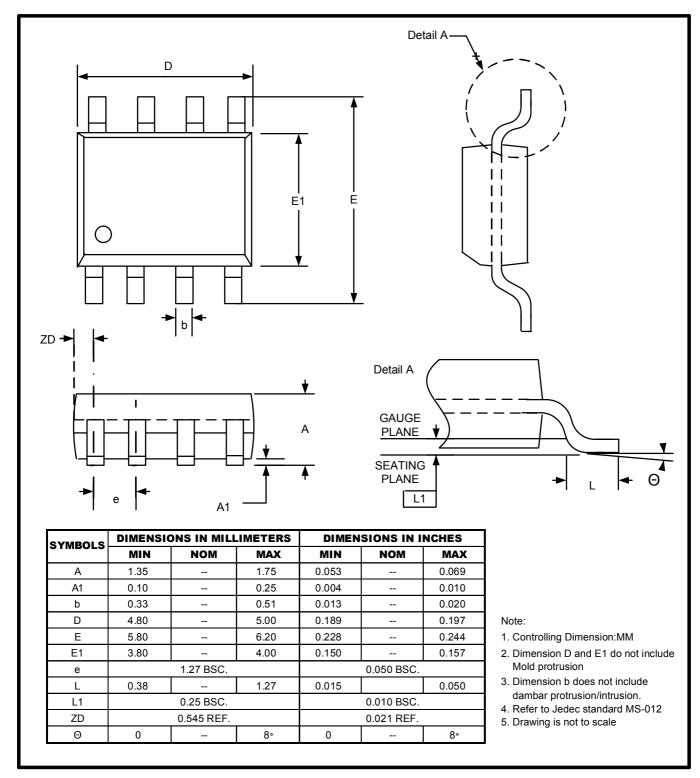
9. Package Information

9.1 SOP23-5



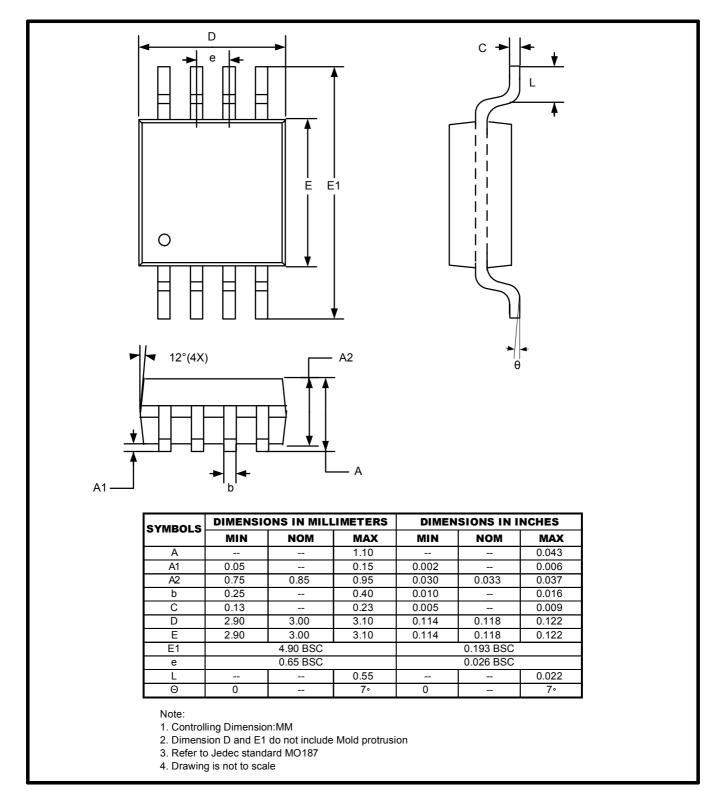


9.2 SOP8





9.3 MSOP8





10. Revision History

Revision	Date	Descriptions
A0	Oct.,2011	Initial Version